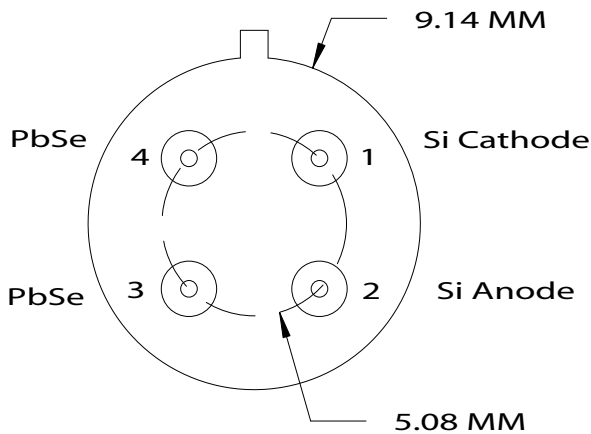


### Si SPECIFICATIONS

TOP Si PV PHOTODIODE  
 ACTIVE AREA - 2.5 MM  
 WAVELENGTH - .3 - 1.0 Microns  
 SHUNT RESISTANCE - 500 Mohms (min) @ 0V  
 SHUNT CAPACITANCE - 400pF (typ)  
 RESPONSIVITY - 0.55A/W @ 850nm  
 $NEP(W/Hz^{1/2}) < 1 \times 10^{-14}$  @ 850nm  
 TIME CONSTANT - 15us @ 0V

### PbSe SPECIFICATIONS

BOTTOM PbSe PC DETECTOR  
 ACTIVE AREA - 2MM X 2MM  
 WAVELENGTH - 1.0 - 4.7 Microns  
 RESISTANCE - .3-1.5 M ohms  
 RESPONSIVITY - >3000V/W  
 $D^*(Pk,1000,1) \times 10^9 - 2.0$   
 TIME CONSTANT - 3us



**NOTE:**

- All TO5 assemblies are hermetically sealed and leak tested
- Custom filters are available
- Other active areas and packages are available
- PbS, Ge and InGaAs materials are available

<b>DO NOT SCALE DRAWING</b>	DRAWN		DATE	<b>N.E.P.</b> NEW ENGLAND PHOTOCONDUCTOR					
	CHECKED		DATE						
	DESIGNER	GG	DATE	<b>FS-2/2.5-5</b> 2 COLOR					
	ENGINEER	PB	DATE						
MATERIAL:	PROJECT ENGINEER		DATE	<b>A</b>	CODE IDENT. NO.	TYPE	<b>1489</b>	REV	
FINISH SPECS:	PROJECT APPROVAL		DATE						
<b>PMB 3/3/09</b>									
SUNSTAR自动化 <a href="http://www.sensor-ic.com/">http://www.sensor-ic.com/</a> TEL: 0755-83376489 FAX: 0755-83376182 E-MAIL: szss20@163.com									